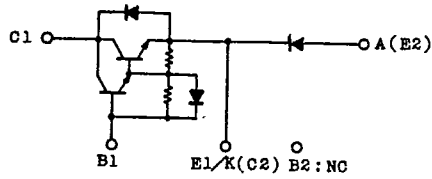




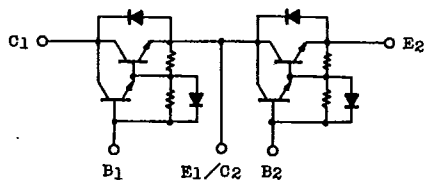
SEMICONDUCTOR

TECHNICAL DATA

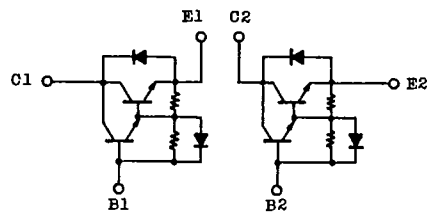
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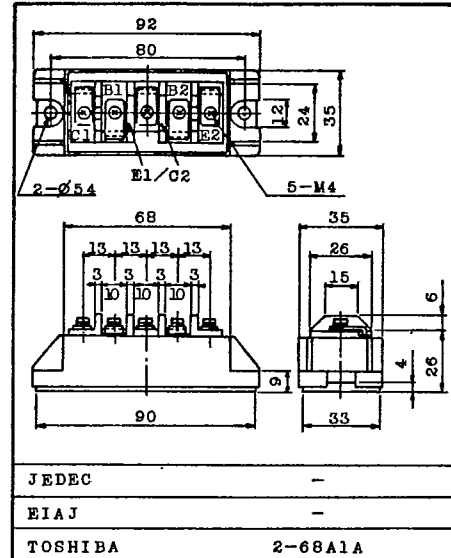


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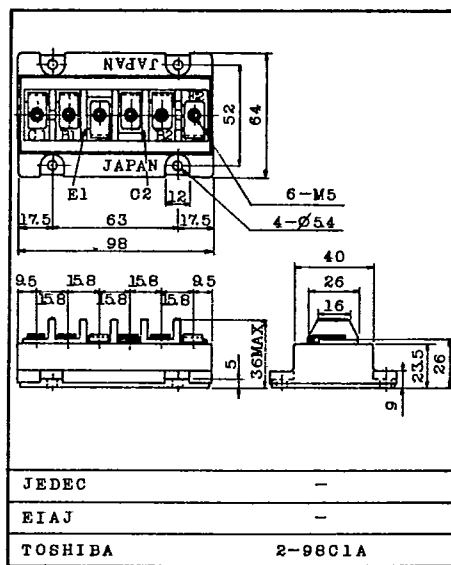


MG100G2DL1

Unit in mm



Unit in mm



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SEMICONDUCTOR

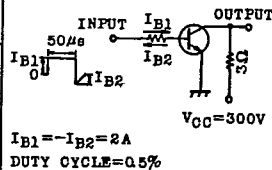
TECHNICAL DATA

MG100G1JL1
MG100G2CL1
MG100G2DL1

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V _{CB0}	600	V
Collector-Emitter Voltage		V _{CE0}	600	V
Collector-Emitter Sustaining Voltage		V _{CEO(SUS)}	450	V
Emitter-Base Voltage		V _{EB0}	6	V
Collector Current	DC	I _C	100	A
	1ms	I _C	200	
	DC	-I _C	100	
Base Current		I _B	5	A
Collector Power Dissipation (Tc=25°C)		P _C	400	W
Junction Temperature		T _j	150	°C
Storage Temperature Range		T _{stg}	-40 ~ 125	°C
Isolation Voltage		V _{isol}	2500(AC 1 Minute)	V
Screw Torque (Terminal/Mounting)		-	20/30	kg.cm

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I _{CB0}	V _{CB} =600V, I _E =0	-	-	2.0	mA
Emitter Cut-off Current		I _{EB0}	V _{EB} =6V, I _C =0	-	-	200	mA
Collector-Emitter Sustaining Voltage		V _{CEO(SUS)}	I _C =0.5A L=40mH	450	-	-	V
DC Current Gain		h _{FE}	V _{CE} =5V, I _C =100A	100	-	-	-
Collector-Emitter Saturation Voltage		V _{CE(sat)}	I _C =100A, I _B =2A	-	-	2.0	V
Base-Emitter Saturation Voltage		V _{BE(sat)}		-	-	2.7	V
Emitter-Collector Voltage		V _{ECO}	I _E =100A, I _B =0	-	-	1.6	V
Reverse Recovery Time		t _{rr}	-I _C =100A, V _{EB} =3V V _{CC} =300V, di/dt=100A/μs	-	-	2.0	μs
Collector Output Capacitance		C _{ob}	V _{CB} =50V, I _E =0 f=1MHz	-	1000	-	pF
Switching Time	Turn-on Time	t _{on}		-	-	2.0	μs
	Storage Time	t _{stg}		-	-	12	
	Fall Time	t _f		-	-	2.0	
Thermal Resistance (Junction to Case)		R _{th(j-c)}	Transistor	-	-	0.31	°C/W
			Diode	-	-	1.3	

TOSHIBA CORPORATION

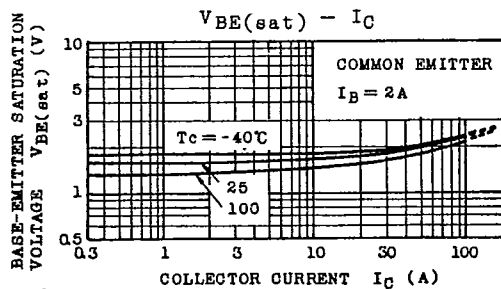
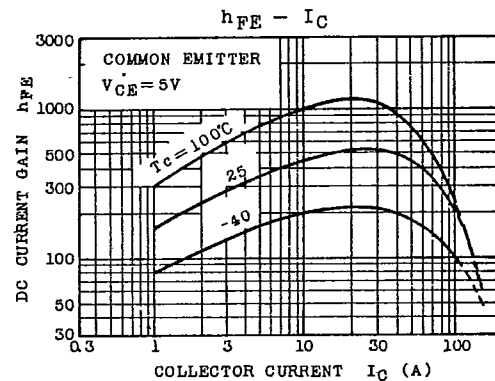
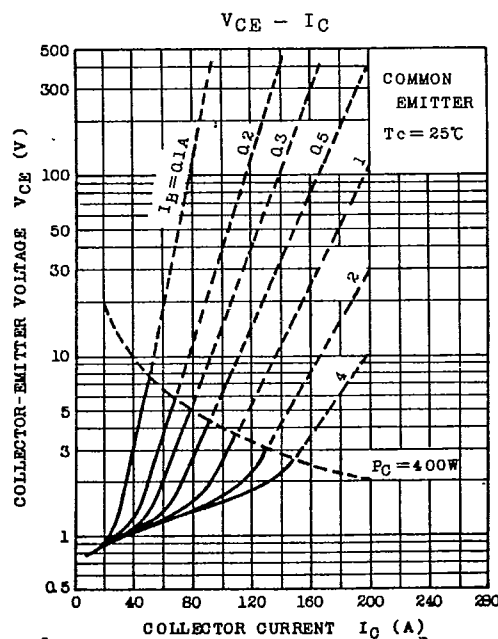
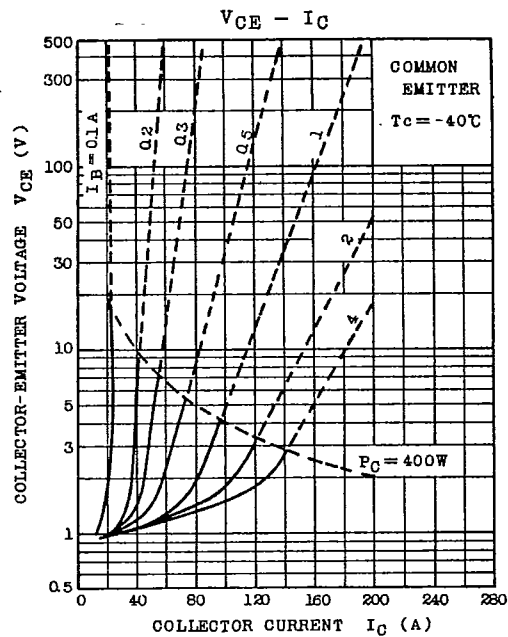
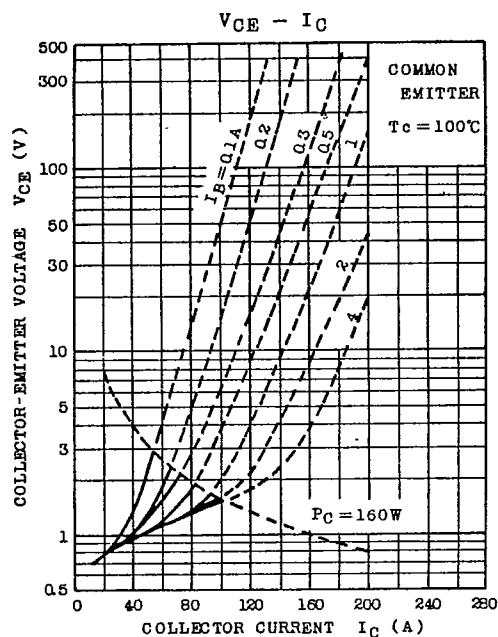
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SEMICONDUCTOR

TECHNICAL DATA

MG100G1JL1
MG100G2CL1
MG100G2DL1



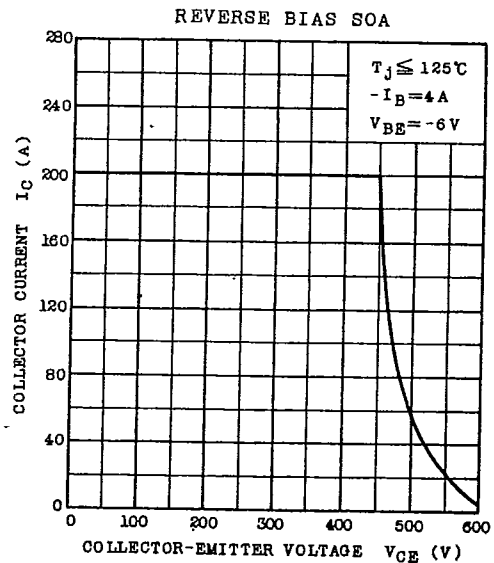
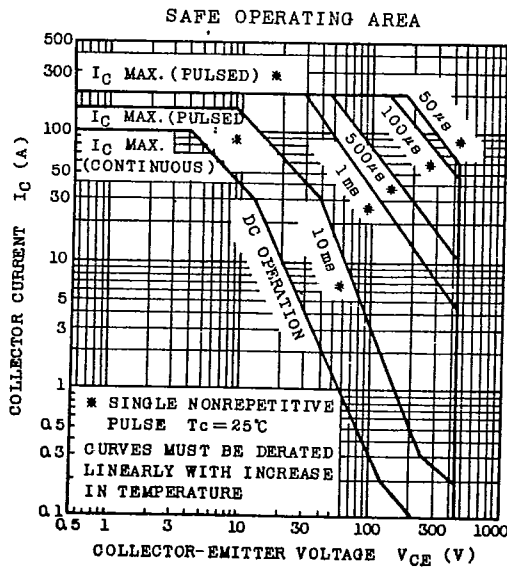
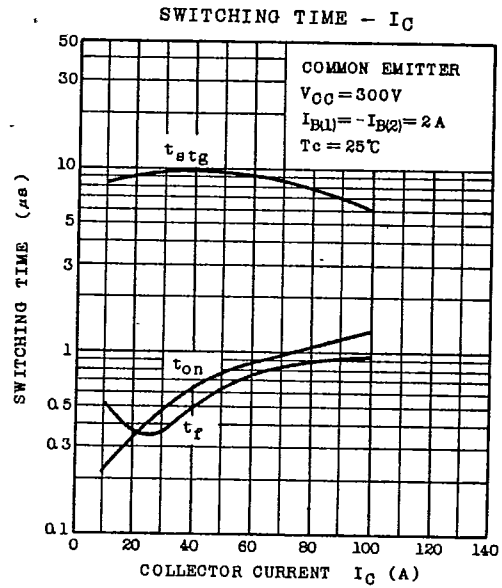
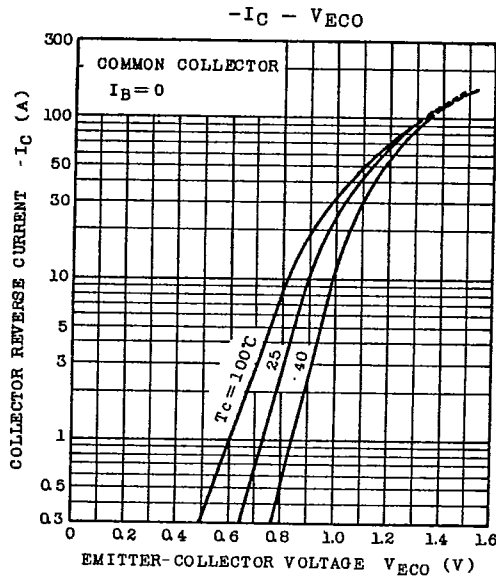
TOSHIBA CORPORATION



SEMICONDUCTOR

TECHNICAL DATA

MG100G1JL1
MG100G2CL1
MG100G2DL1





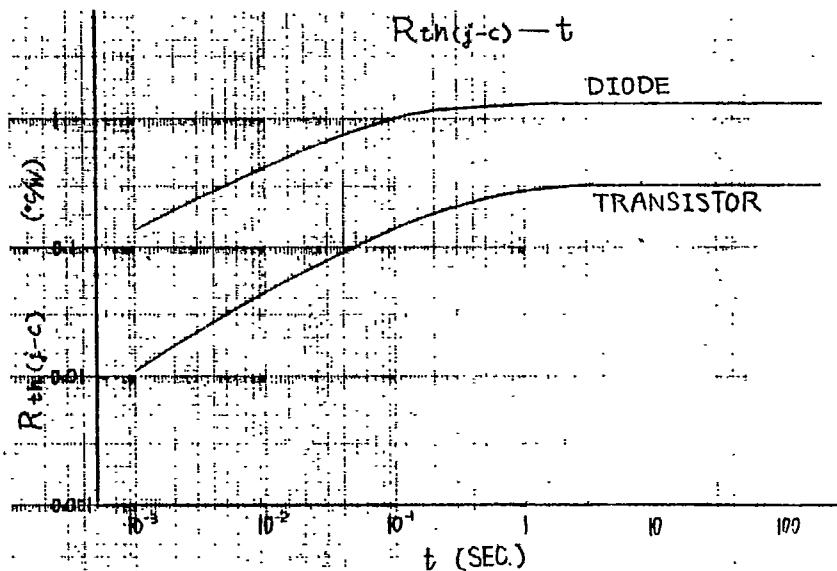
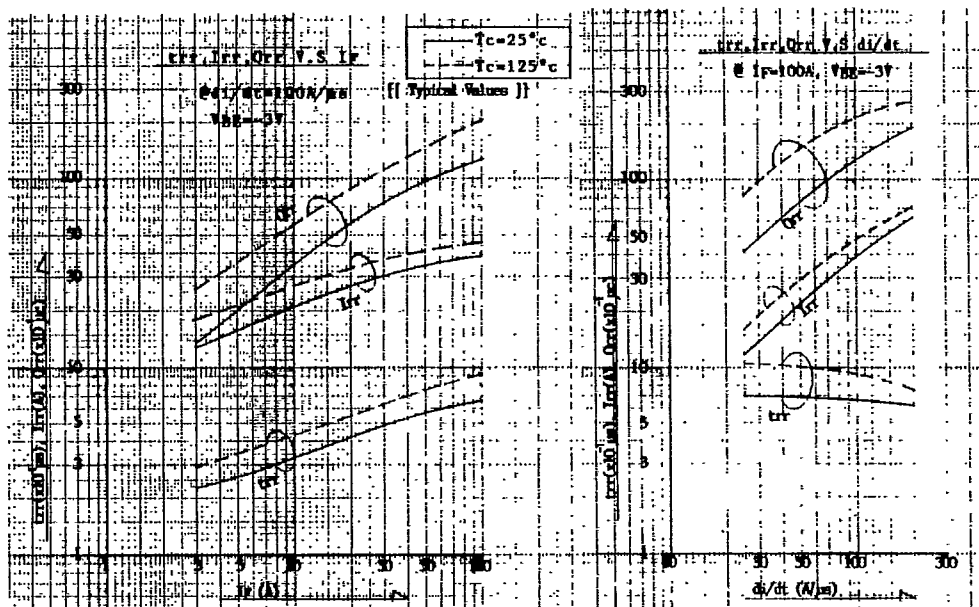
SEMICONDUCTOR

TECHNICAL DATA

MG100G1JL1

MG100G2CL1

MG100G2DL1



TOSHIBA CORPORATION

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